



Session Title:	[WeB1] Power Device III
Session Date:	November 13 (Wed.), 2024
Session Time:	09:00-10:35
Session Room:	Room B (Grand Ballroom 1, 2F, Paradise Hotel Busan)
Session Chair:	Prof. Ho-Jun Lee (Pusan Nat'l Univ., Korea)

[WeB1-1] [Invited]

09:00-09:30

RISE Wide Bandgap Technology for System Integration: Research Activities and Facilities

Jang-Kwon Lim, Jun-Ho Lee, Hithiksha Krishna Murthy, Saeed Akbari, Olof Öber, Magnus Lindberg, Qin Wang, Mietek Bakowski, Linda Johansson, and Klas Brinkfeldt (RISE Research Insts. of Sweden AB, Sweden)

[WeB1-2] [Invited]

09:30-09:55

Current Status of β -Ga₂O₃ Single Crystals by Edge-Defined Film-Fed Growth Method

Si-Young Bae (Pukyong Nat'l Univ., Korea), Yun-Ji Shin, and Seong-Min Jeong (KICET, Korea)

[WeB1-3]

09:55-10:15

Enhancement of GAA-FET by the Optimization of Channel Shape

Min Kyun Sohn, Seong Hyun Lee, Sang-Hoon Kim, Jeong Woo Park, Wangjoo Lee, Jaeseoung Park, Eui-Sang Yu, Jong-Pil Im, Sun Kyu Jung, Min-A Park, Jin Ha Kim, Subin Heo, Song Lee, and Dongwoo Suh (ETRI, Korea)

[WeB1-4]

10:15-10:35

A Low Gate-to-Drain Charge of 1.2 kV SiC DMOSFETs Utilizing a H-Shaped Poly-Si Gate

Dusan Baek, Hyowon Yoon (Pusan Nat'l Univ., Korea), Sangyeob Kim, Gyuhyeok Kang (Kumoh Nat'l Inst. of Tech., Korea), Sumin Park, and Ogyun Seok (Pusan Nat'l Univ., Korea)